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REGULAR PAPERS

**Silicon and Column IV Semiconductors Devices**

Investigation of Symmetric Dual- $k$ Spacer Trigate FinFETs From Delay Perspective .....	P. K. Pal, B. K. Kaushik, and S. Dasgupta	3579
NBTI in Nanoscale MOSFETs—The Ultimate Modeling Benchmark .....	T. Grasser, K. Rott, H. Reisinger, M. Walzl, F. Schanovsky, and B. Kaczer	3586
A Ge Ultrathin-Body n-Channel Tunnel FET: Effects of Surface Orientation .....	K. Alam, S. Takagi, and M. Takenaka	3594
Empirical Model for the Effective Electron Mobility in Silicon Nanowires .....	R. Granzner, V. M. Polyakov, C. Schippel, and F. Schwierz	3601
Improved Interfacial and Electrical Properties of Ge-Based Metal-Oxide-Semiconductor Capacitor With LaTaON Passivation Layer .....	F. Ji, J.-P. Xu, Y. Huang, L. Liu, and P. T. Lai	3608
PBTI-Induced Random Timing Jitter in Circuit-Speed Random Logic .....	J. Lu, G. Jiao, C. Vaz, J. P. Campbell, J. T. Ryan, K. P. Cheung, G. Bersuker, and C. Young	3613
Enhancing Low Temperature Analog Performance of Underlap FinFET at Scaled Gate Lengths .....	A. Nandi, A. K. Saxena, and S. Dasgupta	3619
Characterization of the Depth Distribution and Electrical Activation and Deactivation of Ion Implanted Dopants in Silicon .....	S. Qin	3625
Mobility Improvement Study for 8-Å-EOT HfO <sub>2</sub> UTBB-FD-SOI MOSFET Based on the Direct Extraction of the Back-Channel Mobility .....	L. Trojman, L.-Å. Ragnarsson, and N. Collaert	3632
Strained GeSn p-Channel Metal–Oxide–Semiconductor Field-Effect Transistors With <i>In Situ</i> Si <sub>2</sub> H <sub>6</sub> Surface Passivation: Impact of Sn Composition .....	Y. Liu, J. Yan, H. Wang, Q. Zhang, M. Liu, B. Zhao, C. Zhang, B. Cheng, Y. Hao, and G. Han	3639
A Continuous Electrical Conductivity Model for Monolayer Graphene From Near Intrinsic to Far Extrinsic Region .....	S. Bhattacharya, D. Saha, A. Bid, and S. Mahapatra	3646

(Contents Continued on Page 3577)

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NBTI in Nanoscale MOSFETs—The Ultimate Modeling Benchmark .....	T. Grasser, K. Rott, H. Reisinger, M. Waltl, F. Schanovsky, and B. Kaczer	3586
A Ge Ultrathin-Body n-Channel Tunnel FET: Effects of Surface Orientation .....	K. Alam, S. Takagi, and M. Takenaka	3594
Empirical Model for the Effective Electron Mobility in Silicon Nanowires .....	R. Granzner, V. M. Polyakov, C. Schippel, and F. Schwierz	3601
Improved Interfacial and Electrical Properties of Ge-Based Metal-Oxide-Semiconductor Capacitor With LaTaON Passivation Layer .....	F. Ji, J.-P. Xu, Y. Huang, L. Liu, and P. T. Lai	3608
PBTI-Induced Random Timing Jitter in Circuit-Speed Random Logic .....	J. Lu, G. Jiao, C. Vaz, J. P. Campbell, J. T. Ryan, K. P. Cheung, G. Bersuker, and C. Young	3613
Enhancing Low Temperature Analog Performance of Underlap FinFET at Scaled Gate Lengths .....	A. Nandi, A. K. Saxena, and S. Dasgupta	3619
Characterization of the Depth Distribution and Electrical Activation and Deactivation of Ion Implanted Dopants in Silicon .....	S. Qin	3625
Mobility Improvement Study for 8-Å-EOT HfO <sub>2</sub> UTBB-FD-SOI MOSFET Based on the Direct Extraction of the Back-Channel Mobility .....	L. Trojman, L.-Å. Ragnarsson, and N. Collaert	3632
Strained GeSn p-Channel Metal–Oxide–Semiconductor Field-Effect Transistors With <i>In Situ</i> Si <sub>2</sub> H <sub>6</sub> Surface Passivation: Impact of Sn Composition .....	Y. Liu, J. Yan, H. Wang, Q. Zhang, M. Liu, B. Zhao, C. Zhang, B. Cheng, Y. Hao, and G. Han	3639
A Continuous Electrical Conductivity Model for Monolayer Graphene From Near Intrinsic to Far Extrinsic Region .....	S. Bhattacharya, D. Saha, A. Bid, and S. Mahapatra	3646

(Contents Continued on Page 3577)

Polarity-Controllable Silicon Nanowire Transistors With Dual Threshold Voltages .....	J. Zhang, M. De Marchi, D. Sacchetto, P.-E. Gaillardon, Y. Leblebici, and G. De Michelis	3654
A Steep-Slope Tunnel FET Based SAR Analog-to-Digital Converter .....	M. S. Kim, H. Liu, X. Li, S. Datta, and V. Narayanan	3661
Impact of Channel Orientation on Electrical Properties of Ge p- and n-MOSFETs With 1-nm EOT Al <sub>2</sub> O <sub>3</sub> /GeO <sub>x</sub> /Ge Gate-Stacks Fabricated by Plasma Postoxidation .....	R. Zhang, X. Yu, M. Takenaka, and S. Takagi	3668
Characterization of the Static Thermal Coupling Between Emitter Fingers of Bipolar Transistors .....	S. Lehmann, Y. Zimmermann, A. Pawlak, and M. Schröter	3676
<b>Compound Semiconductor Devices</b>		
Broadband Distortion Cancellation Technique in GaAs HJFET and GaN FET Cascode Amplifier .....	I. Takenaka, S. Takahashi, H. Takahashi, Y. Ando, Y. Kakuta, and C. Sasaoka	3684
Performance Modeling of Bandgap Engineered HgCdTe-Based <i>n</i> Bn Infrared Detectors .....	N. D. Akhavan, G. Jolley, G. A. Umana-Membreno, J. Antoszewski, and L. Faraone	3691
<b>Memory Devices and Technology</b>		
Impact of Scaling on the Performance of HfO <sub>2</sub> -Based Ferroelectric Field Effect Transistors .....	E. Yurchuk, J. Müller, J. Paul, T. Schlosser, D. Martin, R. Hoffmann, S. Müeller, S. Slesazeck, U. Schröeder, R. Boschke, R. van Bentum, and T. Mikolajick	3699
Application of Silicon-Germanium Source Tunnel-FET to Enable Ultralow Power Cellular Neural Network-Based Associative Memory .....	A. R. Trivedi, S. Datta, and S. Mukhopadhyay	3707
A Compact Model for Erratic Event Simulation in Flash Memory Arrays ....	C. Zambelli, T. Vincenzi, and P. Olivo	3716
Impedance Measurement and Characterization of Ag-Ge <sub>30</sub> Se <sub>70</sub> -Based Programmable Metallization Cells .....	D. Mahalanabis, Y. Gonzalez-Velo, H. J. Barnaby, M. N. Kozicki, P. Dandamudi, and S. Vrudhula	3723
Self-Matching SRAM With Embedded OTP Cells in Nanoscale Logic CMOS Technologies .....	S.-Y. Chien, P.-Y. Lin, H.-Y. Chen, C.-J. Lin, and Y.-C. King	3731
A Comparative Study of Single-Poly Embedded Flash Memory Disturbance, Program/Erase Speed, Endurance, and Retention Characteristic .....	S.-H. Song, J. Kim, and C. H. Kim	3737
<b>Thin Film Transistors</b>		
Trapped-Charge-Effect-Based Above-Threshold Current Expressions for Amorphous Silicon TFTs Consistent With Pao-Sah Model .....	H. He, J. He, W. Deng, H. Wang, Y. Liu, and X. Zheng	3744
Two-Stage Degradation of p-Type Polycrystalline Silicon Thin-Film Transistors Under Dynamic Positive Bias Temperature Stress .....	D. Zhang, M. Wang, and X. Lu	3751
Novel Gated-Multiprobe Method for Measuring a Back Electrode Effect in Amorphous Oxide-Based Thin-Film Transistors .....	J. Jeong, J. Kim, and S. M. Jeong	3757
Quantitative Analysis of the Effect of Hydrogen Diffusion from Silicon Oxide Etch-Stopper Layer into Amorphous In–Ga–Zn–O on Thin-Film Transistor .....	T. Toda, D. Wang, J. Jiang, M. P. Hung, and M. Furuta	3762
<b>Optoelectronics, Displays, and Imaging</b>		
UV-Sensitive Low Dark-Count PureB Single-Photon Avalanche Diode .....	L. Qi, K. R. C. Mok, M. Aminian, E. Charbon, and L. K. Nanver	3768
Thickness-Dependent Structural, Optical, and Electrical Characteristics of ZnO:Al Thin Films and Application in OLEDs .....	R. N. Chauhan, C. Singh, R. S. Anand, and J. Kumar	3775
Behavioral Model of Patterned Vertical Alignment Pixel in Active-Matrix Liquid Crystal Displays .....	J.-M. Kim, S.-H. Lee, and S.-W. Lee	3783
Analysis of the Thickness Effect of Undoped Electron-Blocking Layer in Ultraviolet LEDs .....	W.-Y. Lin, T.-Y. Wang, J.-H. Liang, S.-L. Ou, and D.-S. Wu	3790
The Study of Spectral Correction Algorithm of Charge-Coupled Device Array Spectrometer .....	H.-K. Fu, Y.-L. Liu, T.-T. Chen, C.-P. Wang, and P.-T. Chou	3796
MOCVD Grown HgCdTe Barrier Structures for HOT Conditions (July 2014) .....	M. Kopytko, A. Kebłowski, W. Gawron, A. Kowalewski, and A. Rogalski	3803
<b>Solid-State Power and High Voltage Devices</b>		
Substrate-Coupled Cross-Talk Effects on an AlGaN/GaN-on-Si Smart Power IC Platform .....	Q. Jiang, Z. Tang, C. Zhou, S. Yang, and K. J. Chen	3808
TC-LGBTs on the Thin SoI Layer for the High Voltage Monolithic ICs With High Current Density and Latch-Up Immunity .....	J. Zhu, W. Sun, W. Dai, L. Zhang, S. Lu, L. Shi, Y. Yi, S. Zhang, and W. Su	3814

<b>Solid State Device Phenomena</b>	
High-Performance GAA Sidewall-Damascened Sub-10-nm <i>In Situ</i> n <sup>+</sup> -Doped Poly-Si NWs Channels Junctionless FETs .....	P.-Y. Kuo, Y.-H. Lu, and T.-S. Chao 3821
Improved Switching Voltage Variation of Cu Atom Switch for Nonvolatile Programmable Logic .....	N. Banno, M. Tada, T. Sakamoto, K. Okamoto, M. Miyamura, N. Iguchi, and H. Hada 3827
A Four-FET Method for Extracting Mobility in FETs Without Field Oxide .....	A. Majumdar, K.-T. Lee, C.-W. Cheng, K.-T. Shiu, D. K. Sadana, and E. Leobandung 3833
Analytical Models for Delay and Power Analysis of Zero-V <sub>GS</sub> Load Unipolar Thin-Film Transistor Logic Circuits .....	Q. Cui, R. A. Sporea, W. Liu, and X. Guo 3838
<b>Molecular and Organic Devices</b>	
High Mobility Pentacene/C <sub>60</sub> -Based Ambipolar OTFTs by Thickness Optimization of Bottom Pentacene Layer .....	W. Wang, J. Ying, J. Han, and W. Xie 3845
Solution Processed Polymer Near-Infrared Photodiode With Electron and Hole Blockers .....	C. H. Cheung, D. Y. Kim, J. Subbiah, C. M. Amb, J. R. Reynolds, and F. So 3852
<b>Vacuum Electron Devices</b>	
Design of a Novel Dual-Band Gyro-TWT .....	Y. Tang, Y. Luo, Y. Xu, R. Yan, W. Jiang, and Y. Zheng 3858
Transition of Electron Field Emission to Normal Glow Discharge .....	D. Wenger, W. Knapp, B. Hensel, and S. F. Tedde 3864
<b>Emerging Technologies and Devices</b>	
Ballistic Transport in Monolayer Black Phosphorus Transistors .....	F. Liu, Y. Wang, X. Liu, J. Wang, and H. Guo 3871
Dynamic Compact Model of Self-Referenced Magnetic Tunnel Junction .....	J. Azevedo, A. Virazel, A. Bosio, L. Dilillo, P. Girard, J. Alvarez-Hérault, and K. Mackay 3877
Adaptive Compact Magnetic Tunnel Junction Model .....	M. Kazemi, E. Ipek, and E. G. Friedman 3883
<b>BRIEF PAPERS</b>	
Metal-Gate Granularity-Induced Threshold Voltage Variability and Mismatch in Si Gate-All-Around Nanowire n-MOSFETs .....	K. Nayak, S. Agarwal, M. Bajaj, P. J. Oldiges, K. V. R. M. Murali, and V. R. Rao 3892
High-Performance Vertical Gate-All-Around Silicon Nanowire FET With High-κ/Metal Gate .....	Y. Zhai, L. Mathew, R. Rao, M. Palard, S. Chopra, J. G. Ekerdt, L. F. Register, and S. K. Banerjee 3896
Predictive Modeling of Channel Potential in 3-D NAND Flash Memory .....	Y. Kim and M. Kang 3901
Design of Novel High-Q Multipath Parallel-Stacked Inductor .....	V. N. R. Vanukuru and A. Chakravorty 3905
Anomalous Staircase CV Characteristics of InGaSb-on-Insulator FET .....	M. N. K. Alam, M. S. Islam, M. G. Kibria, and M. R. Islam 3910